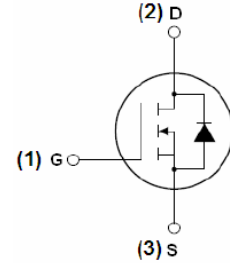


Trench N-Channel PowerMOSFET Wafer Datasheet

FEATURES

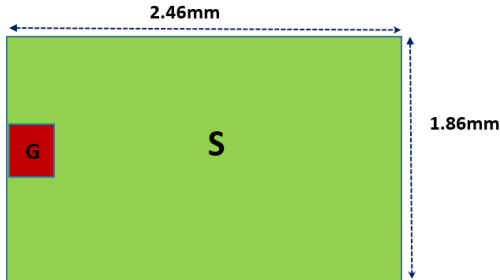
- 100V、30A* , N-channel
- $R_{DS(on)}=30m\Omega(MAX)$
- Ultra low Q_{gd}
- Fast switching



Electrical Characteristics($T_J=25^\circ C$)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	100			V	$V_{GS}=0V, I_D=250\mu A$
$R_{DS(on)}$	Static Drain-Source On-Resistance		20	30	m Ω	$V_{GS}=10V, I_D=15A$
$V_{GS(th)}$	Gate Threshold Voltage	1.0		2.5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			1	μA	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ C$
I_{GSS}	Gate-Body Leakage Current			± 100	nA	$V_{GS}=\pm 20V$
V_{SD}	Body Diode Voltage			1.5	V	$V_{GS}=0V, I_{SD}=30A$
T_J, T_{stg}	Operating and Storage Temperature Range	-55~+150			$^\circ C$	

Mechanical Date

Die Size	2460×1860	μm^2	
Gate Pad Size	300×410		
Source Pad Size	No Passivation		
Scribe Line Size	60	μm	
Wafer Diameter	200	mm	
Wafer Thickness	175	μm	
Passivation Frontside	No Passivation	---	
Source Metallization	AlCu , 4.0	μm	
Drain Metallization	Ti-Ni-Ag 1K-2K-10K	A	
Reject Ink Dot Size	0.51	mm	
Recommended Storage Environment	Store in original container, in desiccated nitrogen, with no contamination		

* Electrical characteristics are reported for the reference packaged part (TO-252/251) and cannot be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.